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# DL4154

## Features

- Fast Switching Speed
- Low Current Leakage
- Low Cost
- Compression Bond Construction
- Surface Mount Application

## Maximum Ratings

- Operation & Storage Temperature: -55°C to +150°C
- Maximum Thermal Resistance: 400k/W Junction to Ambient

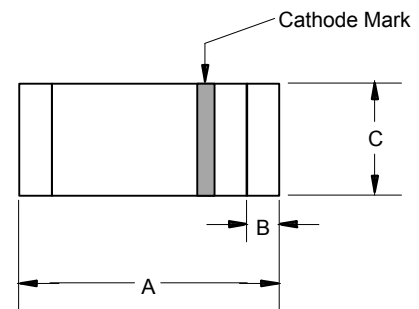
Electrical Characteristics @ 25°C Unless Otherwise Specified

Reverse Voltage	$V_R$	25V	
Peak Reverse Voltage	$V_{RM}$	35V	
Average Rectified Current	$I_O$	150mA	Resistive Load $f > 50\text{Hz}$
Power Dissipation	$P_{TOT}$	500mW	
Junction Temperature	$T_J$	175°C	
Maximum Instantaneous Forward Volt.	$V_F$	1.0V	$I_{FM}=10\text{mA};$ $T_J=25^\circ\text{C}$
Maximum DC Reverse Current At Rated DC Blocking Volt.	$I_R$	0.1uA	$V_R=25\text{V}$ $T_J=25^\circ\text{C}$
Typical Junction Capacitance	$C_J$	4pF	Measured at 1.0MHz, $V_R=4.0\text{V}$
Reverse Recovery Time	$T_{rr}$	2nS	$I_F=10\text{mA}$ $V_R=6\text{V}$ $I_R=1\text{mA}$ $R_L=100\text{OHMS}$

Pulse test: Pulse width 300 usec, Duty cycle 2%.

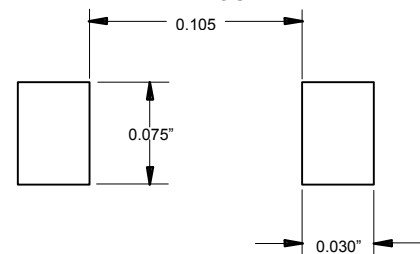
## Schottky Barrier Switching Diode

### MINIMELF



DIM	DIMENSION				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	.134	.142	3.40	3.60	
B	.008	.016	.20	.40	
C	.055	.059	1.40	1.50	

### SUGGESTED SOLDER PAD LAYOUT



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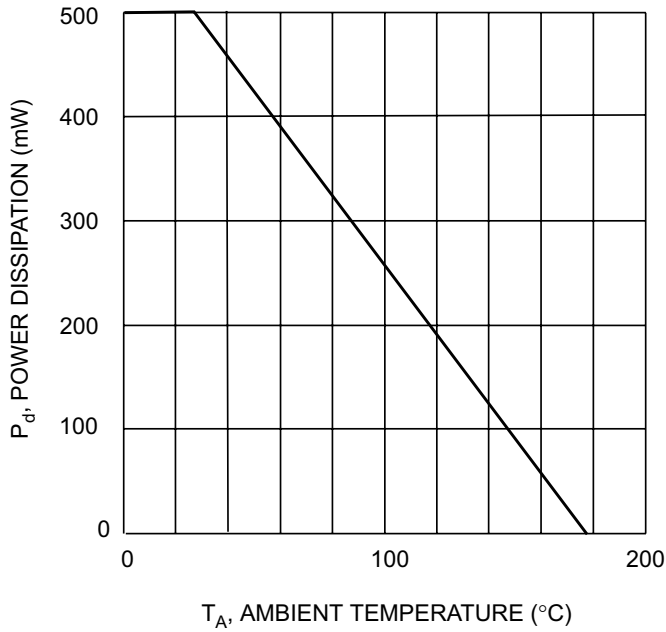


Fig. 1 Power Derating Curve

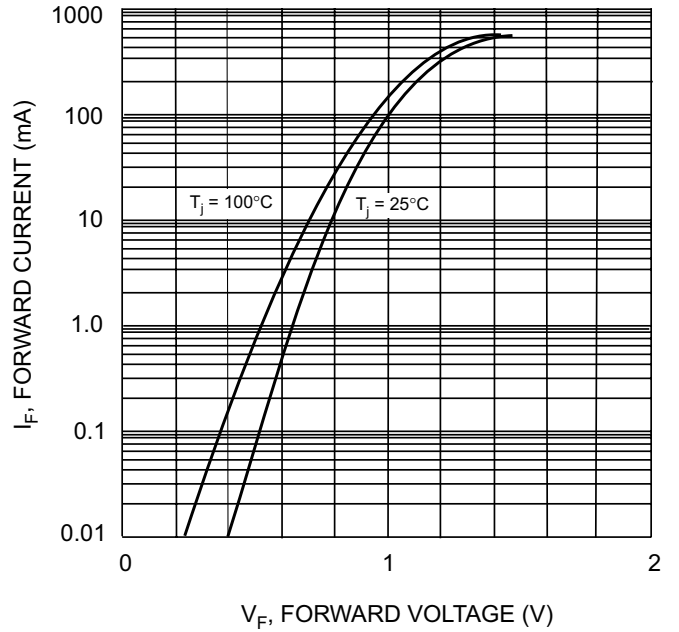


Fig. 2 Forward Characteristics

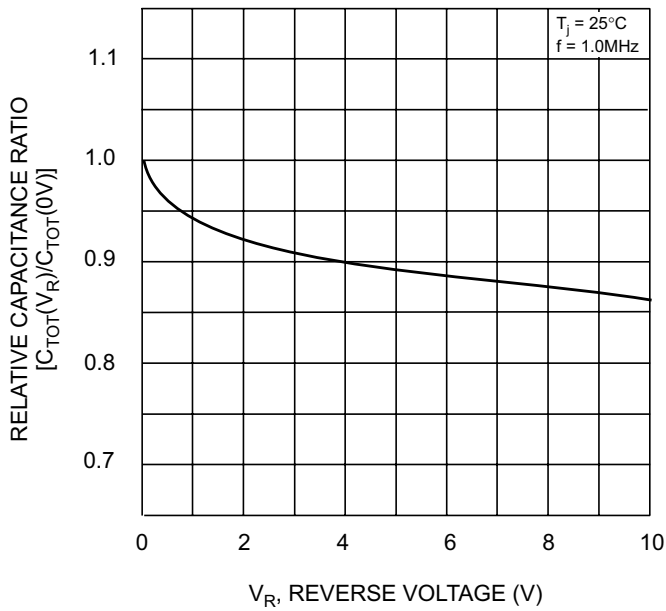


Fig. 3 Relative Capacitance Variation

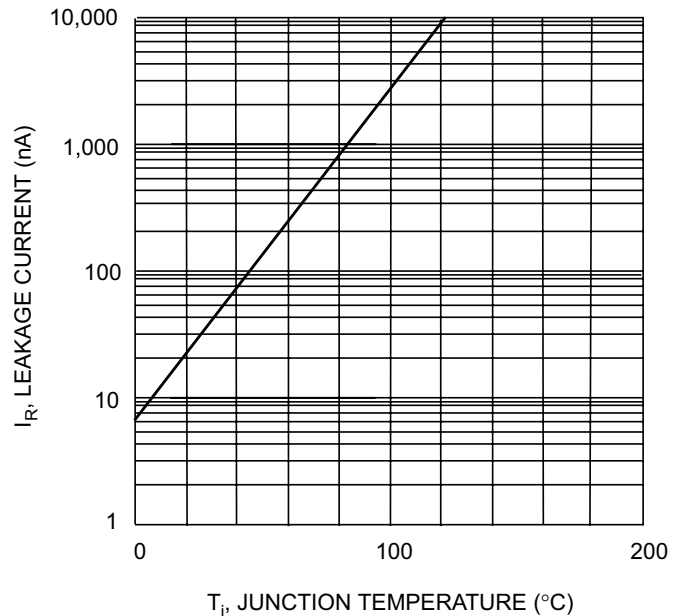


Fig. 4 Leakage Current vs Junction Temperature